

### In the Claims

Please amend claim 5 as follow:

5. (currently amended) A method to remove a silicon oxide material formed during a removal of a photoresist layer configured above a silicon containing material, and the method in removing the silicon oxide material comprising:

an oxygen plasma to remove a majority of the photoresist layer, wherein the silicon oxide material is resulted from a reaction between the silicon containing material and the oxygen plasma; and

an overetch process ~~an ion bombardment method~~ using an inert gas plasma to remove a ~~residual~~ remaining of the photoresist layer and to treat the silicon oxide material.

6. (original) The method to remove a silicon oxide material according to claim 5, wherein the inert gas plasma includes an argon gas plasma.

7. (currently added) The method to remove a silicon oxide material according to claim 5, wherein the overetch process comprises an ion bombardment method.